

P-N Junction with Bias – 2

Minority carrier relations in the neutral regions $\left[x \notin (-x'_p, x'_n) \right]$

Ass.: Steady State (DC bias), no field ($\xi = 0$)

Continuity equations for *P*-side (electrons) $x < -x'_p$

$$\underbrace{\frac{\partial n_p}{\partial t}}_{=0} = \frac{1}{q} \frac{\partial}{\partial x} (j_{n_p}) + \left(\underbrace{G_n}_{=0} - R_n \right)$$

with

$$j_{n_p} = q\mu_n n_p \underbrace{\xi}_{=0} + qD_n \frac{\partial n_p}{\partial x} \quad ; \quad R_n = \frac{n_p - n_{p_0}}{\tau_n} = \frac{\Delta n_p}{\tau_n} .$$

Using the assumptions we obtain

$$0 = \frac{1}{q} \frac{\partial}{\partial x} \left(qD_n \frac{\partial n_p}{\partial x} \right) - \frac{\Delta n_p}{\tau_n}$$

or else because $n_{p_0} = \text{const}$ we can write the ODE for the excess electrons (minority carriers)

$$D_n \frac{d^2 \Delta n_p}{dx^2} - \frac{\Delta n_p}{\tau_n} = 0$$

with the boundary conditions:

a) at $x \rightarrow -\infty$ $\Delta n_p = 0$ because of negligible influence of junction

and

b) at $x = -x'_p$ the density is determined by the law of the junction:

$$n(-x'_p) = n_{p_o} e^{V_a/V_t} .$$

The boundary for the increment, $\Delta n_p(x) = n(x) - n_{p_o}$, of excess carriers is therefore

$$\Delta n_p(-x'_p) = n_{p_o} (e^{V_a/V_t} - 1) .$$

Using these boundary conditions we solve the equation for the increment in the excess carriers and obtain

$$\Delta n_p(x) = n_{p_o} (e^{V_a/V_t} - 1) e^{(x+x'_p)/L_n} \quad ; \quad L_n = \sqrt{D_n \tau_n}$$

This equation is valid for $x \leq -x'_p$. *Please work out the details of the solution.*

Exercise:

For $x \geq x'_n$ the derive following solution

$$\Delta p_n(x) = p_{n_o} (e^{V_a/V_t} - 1) e^{-(x-x'_n)/L_p} \quad ; \quad L_p = \sqrt{D_p \tau_p}$$

The Current Densities

The current density in the neutral region on the p -side ($x \leq -x'_p$) is

$$j_{n_p} = q\mu_n n_p \underset{=0}{\xi} + qD_n \frac{\partial n_p}{\partial x}$$

For the steady state $\frac{\partial}{\partial t}(n_p) = 0$ and with the zero electric field we write

$j_{n_p} = qD_n \frac{dn_p}{dx}$ and considering that $n_{p_o} = \text{const} \neq \varphi(x)$ we can write

$$\frac{dn_p}{dx} = \frac{d(\Delta n_p)}{dx}$$

and thus we have

$$j_{n_p}(x) = qD_n \frac{1}{L_n} n_{p_o} \left(e^{V_a/V_t} - 1 \right) e^{(x+x'_p)/L_n} \quad ; \quad x \leq -x'_p$$

In particular

$$j_{n_p}(-x'_p) = q \frac{D_n}{L_n} n_{p_o} \left(e^{V_a/V_t} - 1 \right) .$$

Exercise

Following the presented approach derive

$$j_{n_p}(x) = q \frac{D_p}{L_p} p_{n_o} \left(e^{V_a/V_t} - 1 \right) e^{-(x-x'_n)/L_p} \quad ; \quad x \geq x'_n$$

and

$$j_{p_n}(x'_n) = q \frac{D_p}{L_p} p_{n_o} \left(e^{V_a/V_t} - 1 \right)$$

The total current density

Considering the discussed above approximations (abrupt junction, depletion, and LLI) we know that the current density is constant (DCD bias) and can write

$$j(x) = j_{n_p}(-x'_p) + j_{p_n}(x'_n)$$

and finally using the previously derived expressions

$$j(x) = q \left(\frac{D_n}{L_n} n_{p_o} + \frac{D_p}{L_p} p_{n_o} \right) (e^{V_a/V_t} - 1)$$

Noting that

$$n_{p_o} = \frac{n_i^2}{N_a^-} \quad \text{and} \quad p_{n_o} = \frac{n_i^2}{N_d^+}$$

we write

$$j(x) = q \underbrace{\left(\frac{D_n}{L_n} \frac{1}{N_a^-} + \frac{D_p}{L_p} \frac{1}{N_d^+} \right)}_{j_s} n_i^2 (e^{V_a/V_t} - 1)$$

The symbol, J_s , represents the saturation current

$$j_s = q \left(\frac{D_n}{L_n} \frac{1}{N_a^-} + \frac{D_p}{L_p} \frac{1}{N_d^+} \right) n_i^2$$

The equation for the DC current density in the $P-N$ structure (idealized) is thus

$$j = j_s \left(e^{V_a/V_t} - 1 \right) .$$

The current through a device with the cross-sectional area, A , is

$$I = A j_s \left(e^{V_a/V_t} - 1 \right)$$

or else

$$I = I_s \left(e^{V_a/V_t} - 1 \right)$$

where the saturation current, I_s , is

$$I_s = q \left(\frac{D_n}{L_n} \frac{1}{N_a^-} + \frac{D_p}{L_p} \frac{1}{N_d^+} \right) n_i^2 A .$$